AiT Semiconductor Inc. www.ait-ic.com

DESCRIPTION

The AM3015 uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

The AM3015 is available in SOP8 package.

ORDERING INFORMATION

Package Type	Part Number			
SOD8	M8	AM3015M8R		
SOP8		AM3015M8VR		
Note	V: Halogen free Package			
Note	R: Tape & Reel			
AiT provides all RoHS products				
Suffix " V " means Halogen free Package				

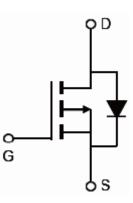
FEATURES

- V_{DS} = -30V, I_D = -15A
- $R_{DS(ON)} < 12m\Omega @ V_{GS}=-10V$
- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- Available in SOP8 Package

APPLICATION

- PWM applications
- Load switch
- Uninterruptible power supply

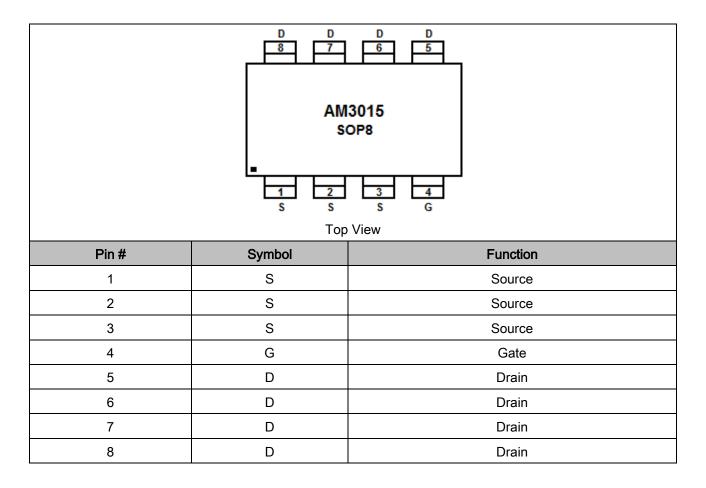
PIN DESCRIPTION



Schematic diagram



PIN DESCRIPTION





ABSOLUTE MAXIMUM RATINGS

T_A=25°C, unless otherwise noted

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V _{DS} , Drain-Source Voltage	-30V
V _{GS} , Gate-Source Voltage	±20V
I _D , Drain Current-Continuous	-15A
IDM, Drain Current-Pulsed NOTE1	-80A
P _D , Maximum Power Dissipation	3.1W
T _J ,T _{STG} , Operating Junction and Storage Temperature Range	-55℃ ~ 150℃

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. NOTE1: Repetitive Rating: Pulse width limited by maximum junction temperature.

THERMAL CHARACTERISTICS

Parameter	Symbol	MAX	Units
Thermal Resistance, Junction-to-Ambient NOTE2	$R_{\theta JA}$	40	°C/W

NOTE2: Surface Mounted on FR4 Board, t \leq 10 sec.



ELECTRICAL CHARACTERISTICS

T_A=25°C, unless otherwise noted

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250µA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	lgss	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics NOTE3						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250µA	-1.0	-1. 5	-2.2	V
Drain-Source On-State Resistance	Rds(on)	V _{GS} =-10V, I _D =-15A	-	8.5	12	mΩ
Forward Transconductance	g fs	V _{DS} =-5V, I _D =-15A	30	-	-	S
Dynamic Characteristics NOTE4						
Input Capacitance	Ciss	V _{DS} =-15V,V _{GS} =0V, F=1.0MHz	-	2900	-	PF
Output Capacitance	Coss		-	410	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	280	-	PF
Switching Characteristics NOTE4						
Turn-on Delay Time	t _{D(ON)}		-	15	-	nS
Turn-on Rise Time	t _R	V _{DD} =-15V,I _D =-10A,	-	11	-	nS
Turn-Off Delay Time	td(OFF)	V_{GS} =-10V, R_{GEN} =3 Ω	-	44	-	nS
Turn-Off Fall Time	t⊧		-	21	-	nS
Total Gate Charge	Q _G	V _{DS} =-15V,I _D =-10A, V _{GS} =-10V	-	48	-	nC
Gate-Source Charge	Q _{GS}		-	12	-	nC
Gate-Drain Charge	Q _{GD}		-	14	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage NOTE3	Vsd	V _{GS} =0V, I _S =-2A	-	-	-1.2	V

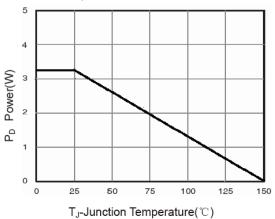
NOTE3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

NOTE4: Guaranteed by design, not subject to production

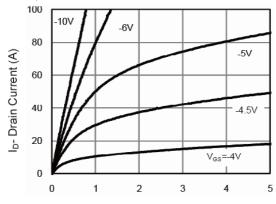


TYPICAL PERFORMANCE CHARACTERISTICS

1. Power Dissipation

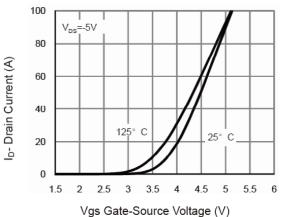


3. Output Characteristics



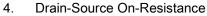
Vds Drain-Source Voltage (V)

5. Transfer Characteristics

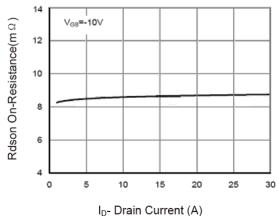


Safe Operation Area 100.0 10us 100µs RDSION I_D- Drain Current (A) 111 limited 1ms 10.0 10ms 0 .1s 1.0 1s T_{J(Max)}=150°C DC T_A=25°C 0.1 10 100 0.1 1

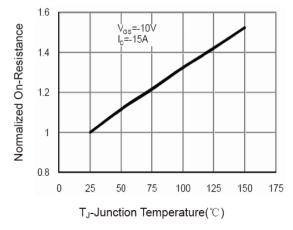
Vds Drain-Source Voltage (V)



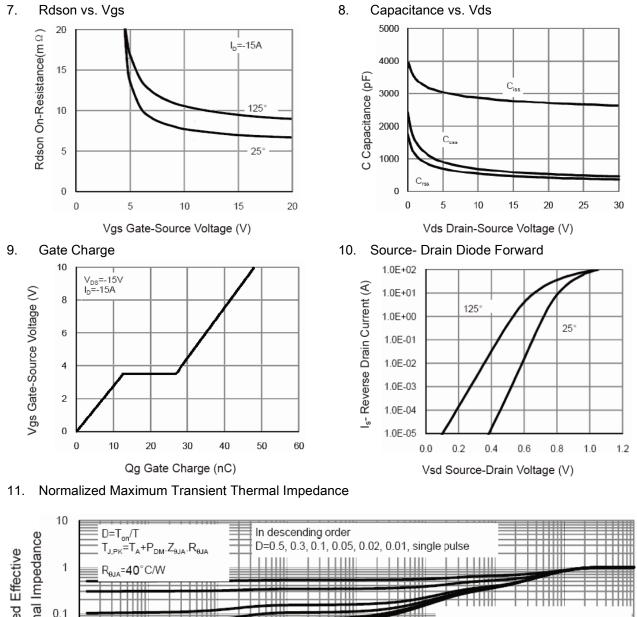
2.

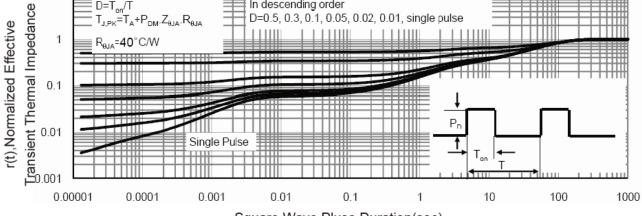


6. Drain-Source On-Resistance









Square Wave Pluse Duration(sec)



t_{d(off)}

INVERTED

t

10%

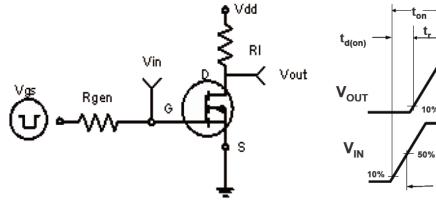
90%

50%

90%

DETAILED INFORMATION

Typical Electrical and Thermal Characteristics



Switching Test Circuit

Switching Waveforms

PULSE WIDTH

t,

10%

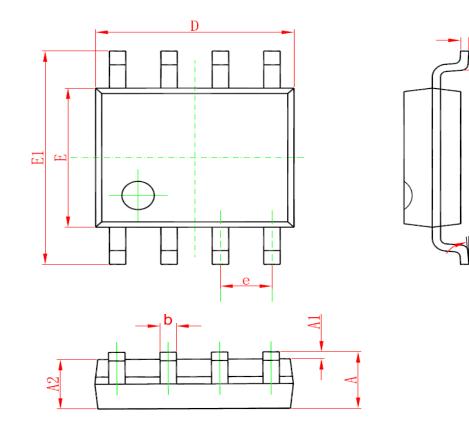
90%



θ

PACKAGE INFORMATION

Dimension in SOP8 (Unit: mm)



Symbol	Min	Max	
А	1.350	1.750	
A1	0.100	0.250	
A2	1.350	1.550	
b	0.330	0.510	
С	0.170	0.250	
D	4.700	5.100	
E	3.800	4.000	
E1	5.800	6.200	
е	1.270(BSC)		
L	0.400	1.270	
θ	0°	8°	



IMPORTANT NOTICE

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